arXiv:1010.5162v1 [cond-mat.mes-hall] 25 Oct 2010

Diffusion thermopower of a $p-$type Si/Si$_{1-x}$Ge$_x$ heterostructure at zero magnetic field

Tran Doan Huan and **Nguyen Phuc Hai***

Institute of Engineering Physics, Hanoi University of Technology, 1 Dai Co Viet Rd., Hanoi, Vietnam
Faculty of Engineering, Katholieke University of Leuven, Kasteelpark Arenberg 44, B-3001 Heverlee (Leuven), Belgium

Key words Diffusion thermopower, hole, scattering, heterostructure.
PACS 72.20.Pa, 73-40.Kp

We calculate the diffusion thermopower of the degenerate two-dimensional hole gas in a $p-$type Si/Si$_{1-x}$Ge$_x$ lattice mismatched heterostructure at low temperatures and zero magnetic field. The effects of possible scatterings, e.g. remote impurity, alloy disorder, interface roughness, deformation potential, and random piezoelectric on the hole mobility and the diffusion thermopower are examined. Calculated results are well fitted to the experimental data recently reported. In addition, we predict a possibility for the diffusion thermopower to change its sign as the SiGe layer thickness changes, the effect has not been discussed yet.

Copyright line will be provided by the publisher

1 Introduction

In a recent experiment, the thermopower of the two-dimensional (2D) hole gas in a $p-$type Si/Si$_{0.88}$Ge$_{0.12}$ heterostructure (HS) were reported [1]. At very low temperature, the total thermopower S, approximated by the diffusion thermopower S^{d}, was explained by a *phenomenological* model without calculations starting from the microscopic level [1]. Since many theoretical studies [2, 3] of the diffusion thermopower are available, it may be interesting if one can use them to examine the reported data.

Among the scatterings determining diffusion thermopower, impurity doping and interface roughness are normally studied [2, 3]. However, proper considerations for diffusion thermopower due to deformation potential and alloy disorder, to the best of our knowledge, are unavailable. Further, some assumptions used in the existing studies are actually weak. First, the potential barrier at the HS's interface is always assumed to be infinite [2, 3], although it is small, thus changes the transport properties of the HS [3, 4]. Next, deformation potential scattering limiting the 2D hole mobility is always based on the idea that the holes and the electrons undergo the same deformation potential [5]. This assumption was indicated [4] to be invalid, and the properly derived deformation scattering was found [4] to strongly limit the 2D hole mobility. Consequently, one may interest in studying the diffusion thermopower determined by this scattering. Lastly, a study of the diffusion thermopower caused by random piezoelectric field, the recently introduced scattering [4], is open. This scattering was found [6] to cause a sign change of the diffusion thermopower in an $n-$type GaAs quantum well as the well thickness varies. Even though piezoelectric scattering in SiGe alloy is weak [4], a study of the diffusion thermopower associated with it may be useful.

In this paper, we calculate the diffusion thermopower of the 2D hole gas in a $p-$type Si/Si$_{0.88}$Ge$_{0.12}$ HS with finite barrier. The scatterings to be considered are remote impurity, alloy disorder, interface roughness, piezoelectric, and the properly derived deformation potential. Calculated diffusion thermopower is given in comparison with experiment [1]. We also discuss the possibility for the diffusion thermopower to change its sign as the SiGe layer thickness varies.

---

* Corresponding author, email: hainp-iep@mail.hut.edu.vn

2 Diffusion thermopower

The total thermopower S is defined by $\mathcal{E} = S\nabla T$ in the presence of a temperature gradient ∇T and an electric field $\mathcal{E}$. At the limit of weak coupling, the total thermopower S of a degenerate 2D gas is $S = S^{\rm d} + S^{\rm g}$, where $S^{\rm d}$ and $S^{\rm g}$ are the diffusion and phonon-drag components, respectively [1, 2, 3]. At low temperature T, $S^{\rm d} \propto T$ [1, 2, 3], while $S^{\rm g}$ has a more complex behavior depending on the carrier-phonon scattering. For deformation potential scattering, $S^{\rm g} \propto T^6$ [7], while for piezoelectric scattering, $S^{\rm g} \propto T^4$ [8]. In the former case, $S^{\rm g}$ dominates as $T \leq 1{\rm K}$, while in the latter, $S^{\rm d}$ dominates below $0.5{\rm K}$. Thus, as $T < 0.5{\rm K}$, one can consider $S^{\rm d}$ as the total thermopower, which can be measured [1]. For elastic scatterings, the diffusion thermopower $S^{\rm d}$ of a 2D hole gas at zero magnetic field is given by [2, 3]:

$$S^{\rm d} = \frac{\pi^2 k_{\rm B}^2 T}{3|e|}\left[\frac{d\ln\sigma(E)}{dE}\right]_{E=E_{\rm F}}, \tag{1}$$

where $|e|$ is the hole charge, $k_{\rm B}$ Boltzmann constant, $E_{\rm F} = \hbar^2 k_{\rm F}^2/2m^*$ the Fermi energy, $k_{\rm F} = \sqrt{2\pi p_{\rm S}}$ Fermi wave number, and m^* the hole effective mass. In Eq. (1), the $\sigma(E)$ is the conductivity given by $\sigma(E) = p_{\rm S}(E)e^2\tau(E)/m^*$ with $\tau(E)$ is relaxation time and $p_{\rm S}(E) = Em^*/\pi\hbar^2$ the 2D hole density [2, 3]. It is always assumed [2, 3] that $\tau(E) \propto E^p$, so the Eq. (1) can be rewritten by Mott formula [2, 3]:

$$S^{\rm d} = \frac{\pi^2 k_{\rm B}^2 T}{3|e|E_{\rm F}}(p+1), \tag{2}$$

with the scattering parameter p defined by [2, 3]:

$$p = \frac{E_{\rm F}}{\tau(E_{\rm F})}\left[\frac{d\tau(E)}{dE}\right]_{E=E_{\rm F}}. \tag{3}$$

The hole gas in our HS, as will be seen later, is expected to undergo simultaneously remote impurity, alloy disorder, interface roughness, deformation potential, and piezoelectric scatterings. In this case, the total relaxation time $\tau(E)$ is given by the Matthiessens rule [9]:

$$\frac{1}{\tau(E)} = \frac{1}{\tau_{\rm RI}(E)} + \frac{1}{\tau_{\rm AD}(E)} + \frac{1}{\tau_{\rm IFR}(E)} + \frac{1}{\tau_{\rm DP}(E)} + \frac{1}{\tau_{\rm PE}(E)}, \tag{4}$$

where $\tau_{\rm RI}(E)$, $\tau_{\rm AD}(E)$, $\tau_{\rm IFR}(E)$, $\tau_{\rm DP}(E)$, and $\tau_{\rm PE}(E)$ are the relaxation times due to the scatterings listed above, respectively.

It could be seen from the Eqs. (2) and (4), that the total diffusion thermopower $S^{\rm d}$ of a 2D system, which undergoes more than one scatterings, is specified *not only* by the scattering strengths, *but also* the energy dependence of the relaxation time $\tau(E)$ at $E = E_{\rm F}$. In terms of the corresponding autocorrelation functions $\langle|U(\boldsymbol{q})|^2\rangle$, they are expressed by [4, 6]:

$$\frac{1}{\tau(E)} = \frac{1}{(2\pi)^2\hbar E}\int_0^{2q} dq' \int_0^{2\pi} d\theta\, \frac{q'^2}{\sqrt{4q^2 - q'^2}}\frac{\langle|U(\boldsymbol{q'})|^2\rangle}{\epsilon^2(q')}, \tag{5}$$

where $\boldsymbol{q'} = (q', \theta')$, $E = \hbar^2 q^2/2m^*$ is the energy corresponding to wave vector $\boldsymbol{q} = (q, \theta)$. The dielectric function $\epsilon(q)$ in Eq. (5) is given at zero temperature within the random phase approximation by [9]

$$\epsilon(q) = 1 + \frac{q_{\rm TF}}{q}F_{\rm S}(q)\,[1 - G(q)] \quad \text{for } q \leq 2k_{\rm F}, \tag{6}$$

with $q_{\rm TF} = 2m^*e^2/\epsilon_{\rm L}\hbar^2$ is the inverse 2D Thomas-Fermi screening length, $\epsilon_{\rm L}$ the dielectric constant of the HS, and the function $G(q) = q/2\sqrt{q^2 + 4k_{\rm F}^2}$ in Eq. (6) allows for the local field corrections associated with the many-body interactions of the 2D hole gas [9]. The form factor $F_{\rm S}(q)$ is defined by [4, 10]:

$$F_{\rm S}(q) = \int_{-\infty}^{+\infty} dz \int_{-\infty}^{+\infty} dz' |\zeta(z)|^2 |\zeta(z')|^2 e^{-q|z-z'|}, \tag{7}$$

where $\zeta(z)$ and $\zeta(z')$ are the wave functions representing the two holes having interaction (7). An explicit expression for $F_{\rm S}(q)$ will be given in the Eq. (10), thus $\langle |U(\boldsymbol{q})|^2\rangle$ is all needed for specifying $\tau(E)$.

3 Autocorrelation functions for the scattering mechanisms

Scattering by a random field can be specified by its autocorrelation function in the wave vector space $\langle |U(\boldsymbol{q})|^2\rangle$ [9]. Here the angular brackets stand for an ensemble average over the fluctuations of the 2D Fourier transform of the random scattering field $U(\boldsymbol{q})$, given by [4, 9]:

$$U(\boldsymbol{q}) = \int_{-\infty}^{+\infty} dz\, |\zeta(z)|^2 U(\boldsymbol{q}, z). \tag{8}$$

In our HS, the 2D hole gas is confined by a triangular potential [1, 11] located along the growth direction chosen as the z axis with the Si/SiGe interface locates at $z = 0$. It has been shown [12] that for the finite barrier potential V_0, the lowest subband may be very well described by the modified Fang-Howard wave function [9, 12, 10]:

$$\zeta(z) = \begin{cases} A\kappa^{1/2} e^{\kappa z/2} & \text{for } z < 0, \\ Bk^{1/2}(kz + c)e^{-kz/2} & \text{for } z > 0, \end{cases} \tag{9}$$

in which k and κ are half of the wave numbers in the well and barrier, respectively. Further, $A,\ B,\ c,\ \kappa,$ and k are the variational parameters to be determined by minimizing the ground state energy connecting to V_0 [12]. Detailed expressions to be minimized could be found elsewhere [4, 9, 10, 12, 13].

Using Eq. (9), the form factor $F_{\rm S}(q)$ in (7) can be given in term of $t = q/k$ and $a = \kappa/k$ by [4, 10]

$$F_{\rm S}(t) = \frac{A^4 a}{t + a} + 2A^2B^2 a \frac{2 + 2c(t+1) + c^2(t+1)^2}{(t+a)(t+1)^3} + \frac{B^4}{2(t+1)^3}\Big[2(c^4 + 4c^3 + 8c^2 + 8c + 4) + t\,(4c^4 + 12c^3 + 18c^2 + 18c + 9) + t^2(2c^4 + 4c^3 + 6c^2 + 6c + 3)\Big]. \tag{10}$$

Our HS is doped by an impurity sheet of thickness $L_{\rm I}$ supplying a scattering source [1, 11]. This impurity sheet follows a spacer layer of thickness $L_{\rm S}$ grown on the top of the SiGe layer of thickness L [11]. Thus, the first autocorrelation function we have to specify should be [9, 12, 13]:

$$\langle |U_{\rm RI}(\boldsymbol{q})|^2\rangle = \left(\frac{2\pi e^2}{\epsilon_L q}\right)^2 \frac{q}{q + q_{\rm I}} \int_{L+L_{\rm S}}^{L+L_{\rm S}+L_{\rm I}} dz_i n_{\rm I}(z_i) F_{\rm I}^2\,(q, z_i) \tag{11}$$

where $F_{\rm I}(q, z_i)$ is the remote impurity form factor of a 2D impurity sheet located at z_i defined by [9, 12]:

$$F_{\rm I}\,(q, z_i) = \int_{-\infty}^{\infty} dz |\zeta(z)|^2 e^{-q|z - z_i|} \tag{12}$$

while $n_{\rm I}(z)$ is the impurity density at z_i, which is $n_{\rm I}$ as $L + L_{\rm S} < z_i < L + L_{\rm S} + L_{\rm I}$ and zero otherwise.

Further, it was indicated [14] that at high impurity doping level, the impurity distribution is not completely random. Due to the Coulomb interaction among the charged impurities during the sample growth, the impurity diffusion tends to diminish the probability of large fluctuations of the impurity density [15]. The so-called impurity correlation effect can be taken [13, 16] by adding to the autocorrelation function a screening-like factor $q/(q + q_{\rm I})$ in term of the inverse statistical-screening radius $q_{\rm I}$ defined by [13, 16]

$$q_{\rm I} = \frac{2\pi e^2 n_{\rm I} L_{\rm I}}{\epsilon_L k_{\rm B} T_0}. \tag{13}$$

In the above expression, $T_0 \sim 1000K$ is the freezing temperature of the impurity system [13, 16].

By plugging Eq. (9) into Eq. (12), and then putting results into Eq. (11), we obtain $\langle|U_{\mathrm{RI}}(\boldsymbol{q})|^2\rangle$ as:

$$\langle|U_{\mathrm{RI}}(\boldsymbol{q})|^2\rangle= \left(\frac{2\pi e^2}{\epsilon_L q}\right)^2 \frac{n_{\mathrm{I}}}{k}\frac{q}{q+q_{\mathrm{I}}}\left\{\frac{1}{2}\left[Q_1^2\left(\frac{q}{k},s\right)-Q_1^2\left(\frac{q}{k},d\right)\right]+4B^2\left[Q_1\left(\frac{q}{k},s\right)Q_2\left(\frac{q}{k},s\right)\right.\right.$$
$$\left.\left.-Q_1\left(\frac{q}{k},d\right)Q_2\left(\frac{q}{k},d\right)\right]+B^4\left[Q_3\left(\frac{q}{k},s\right)-Q_3\left(\frac{q}{k},d\right)\right]\right\} \quad (14)$$

with $s=k(L+L_{\mathrm{S}}), d=k(L+L_{\mathrm{S}}+L_{\mathrm{I}})$ and the auxiliary functions defined by:

$$Q_1(t,v)=\frac{e^{-tv}}{\sqrt{t}}\left\{\frac{A^2a}{t+a}+B^2\left[\frac{c^2}{1-t}+\frac{2c}{(1-t)^2}+\frac{2}{(1-t)^3}\right]\right\}, \quad (15)$$

$$Q_2(t,v)=\frac{e^{-v}\sqrt{t^3}}{1+t}\left[\frac{(c+v)^2}{t^2-1}+\frac{2c(t-3)}{(t^2-1)^2}+\frac{2v(t^3-3t^2-t+3)}{(t^2-1)^3}+\frac{4(t^2-2t+3)}{(t^2-1)^3}\right], \quad (16)$$

$$Q_3(t,v)=e^{-2v}t^2\left[\frac{3t^8-20t^6+66t^4-84t^2+163}{(t^2-1)^6}+\frac{2(c+v)(3t^6-17t^4+41t^2-91)}{(t^2-1)^5}\right.$$
$$\left.+\frac{2(c+v)^2(3t^4-14t^2+43)}{(t^2-1)^4}+\frac{4(c+v)^3(t^2-5)}{(t^2-1)^3}+\frac{2(c+v)^4}{(t^2-1)^2}\right]. \quad (17)$$

The other autocorrelation functions can be taken from Ref. [4]. For alloy disorder, it is given by [4]:

$$\langle|U_{\mathrm{AD}}(\boldsymbol{q})|^2\rangle=x(1-x)u_{\mathrm{al}}^2\Omega_0\frac{B^4b^2}{L}\left[c^4p_0(2b)+4c^3p_1(2b)+6c^2p_2(2b)+4cp_3(2b)+p_4(2b)\right], \quad (18)$$

where x denotes the Ge content of the SiGe alloy, u_{Al} is the alloy potential. The volume occupied by one alloy atom is given by $\Omega_0=a_{\mathrm{Al}}^3/8$, with a_{Al} the lattice constant of the alloy. The auxiliary functions $p_l(v)$ ($l=0-4$) of the dimensionless variables v and b used here are defined by [4]

$$p_l(v)=\frac{b^l}{v^{l+1}}\left(1-e^{-v}\sum_{j=0}^{l}\frac{v^j}{j!}\right). \quad (19)$$

The autocorrelation function of interface roughness scattering is given by [4]:

$$\langle|U_{\mathrm{IFR}}(\boldsymbol{q})|^2\rangle=\left(\frac{4\pi e^2}{\epsilon_L}\right)^2 B^4\left[n_{\mathrm{D}}\left(c^2+2c+2\right)+\frac{p_{\mathrm{S}}B^2}{2}\left(c^4+4c^3+8c^2+8c+4\right)\right]^2\langle|\Delta_{\boldsymbol{q}}|^2\rangle \quad (20)$$

where n_{D} is the depletion charge density. $\langle|\Delta_{\boldsymbol{q}}|^2\rangle$ is the spectral distribution of the interface profile usually assumed [2, 9] to be in Gaussian form specified by roughness amplitude Δ and correlation length Λ as:

$$\langle|\Delta_{\boldsymbol{q}}|^2\rangle=\pi\Delta^2\Lambda^2\exp\left(-\frac{q^2\Lambda^2}{4}\right). \quad (21)$$

Deformation potential scattering is a combined effect of lattice mismatch, which gives rise a strain field ϵ, and interface roughness [17, 18]. In the previous studies [5], it has always been assumed that the deformation potential experienced by the holes in the valence band is identical to that experienced by electrons in the conduction band [17] with a different coupling constant Ξ. This assumption is, in fact, invalid. In particular, while the deformation potential for the electrons in the conduction band is fixed by a single component ϵ_{zz} of the strain field, that for the holes in the valence band must be fixed by all three diagonal components of ϵ [19]. Thus, the autocorrelation function for the deformation potential scattering for the holes needs to be modified to have the following form [4]:

$$\begin{aligned}\langle|U_{\mathrm{DP}}(\boldsymbol{q})|^2\rangle \;&= \left(\frac{B^2b^2\alpha\epsilon_{\|}}{2L}\right)^2 t^2\Big[c^2p_0(b+bt)+2cp_1(b+bt)+p_2(b+bt)\Big]^2\times\\ &\times\left[\frac{3}{2}[b_{\mathrm{s}}(K+1)]^2(1+\sin^4\theta+\cos^4\theta)+\left(\frac{d_{\mathrm{s}}G}{4c_{44}}\right)^2\left(1+\frac{\sin^2 2\theta}{4}\right)\right]\langle|\Delta_{\boldsymbol{q}}|^2\rangle,\end{aligned}\tag{22}$$

in which $b = kL$, $\epsilon_{\|} = (a_{\mathrm{Si}} - a_{\mathrm{Al}})/a_{\mathrm{Al}}$ is the in-plane strain, b_{s} and d_{s} the shear deformation potential constants. The anisotropy ratio $\alpha = 2c_{44}/(c_{11} - c_{12})$ and the elastic constants $K = 2c_{12}/c_{11}$, $G = 2(K+1)(c_{11} - c_{12})$ are deduced from the elastic stiffness constants of the SiGe alloy c_{11}, c_{12}, and c_{44}.

Similarly, random piezoelectric scattering is a combined effect of lattice mismatch and interface roughness [4]. The other requirement for this scattering is the piezoelectricity of the strained SiGe layer, which has recently been found [20]. Because of the interface roughness, the off-diagonal components of the strain field in the SiGe layer become randomly fluctuating [4, 17]. Therefore, they induce inside the SiGe layer a fluctuating density of bulk like piezoelectric charges supplying a scattering source. The autocorrelation function for piezoelectric scattering in our HS has been derived by Ref. [4] as:

$$\langle|U_{\mathrm{PE}}(\boldsymbol{q})|^2\rangle = \left(\frac{3\pi e e_{14}G\alpha\epsilon_{\|}\sin 2\theta}{8\epsilon_{\mathrm{L}}c_{44}}\right)^2 F_{\mathrm{PE}}^2\left(\frac{q}{k}\right)\langle|\Delta_{\boldsymbol{q}}|^2\rangle,\tag{23}$$

with e_{14} is the piezoelectric constant of the SiGe alloy [4, 20]. The piezoelectric form factor $F_{\mathrm{PE}}(t)$ appearing in the above equation is given by [4]

$$\begin{aligned}F_{\mathrm{PE}}(t) = \frac{A^2a}{t+a}\left(1-e^{-2bt}\right) + B^2b\bigg\{&\frac{2c^2t}{t+1}+\frac{4ct}{(t+1)^2}+\frac{4t}{(t+1)^3}+c^2(1-2bt)p_0(b+bt)\\ &+2c(1+ct-2bt)p_1(b+bt)+(1+4ct-2bt)p_2(b+bt)+2tp_3(b+bt)\\ &-e^{-2bt}\Big[c^2p_0(b-bt)+2cp_1(b-bt)+p_2(b-bt)\Big]\bigg\}.\end{aligned}\tag{24}$$

The background impurity scattering examined in some previous studies [2, 3] is not considered here. The reason is that our HS has only an impurity sheet separated from the well by a spacer of thickness $L_{\mathrm{S}} = 120$Å, but no intentional background impurity [1, 11]. Thus, the Eqs. (11), (18), (20), (22), and (23) supply all needed for specifying the relaxation time using the Eq. (5).

4 Numerical results and discussions

4.1 Comparison to experiment

We now compare calculated S^{d} to some experimental data for the thermopower S ($T < 0.5$K) of the 2D hole gas in a $p-$type Si/Si$_{0.88}$Ge$_{0.12}$ HS reported on the Fig. 6 of the Ref. [1]. This HS, which is the sample CVD191 used in the Refs. [1, 11], is composed by a strained Si$_{0.88}$Ge$_{0.12}$ layer of thickness L grown on a Si substrate. A spacer of thickness L_{S} followed by an impurity sheet of thickness L_{I} is placed on the top of the well. At $p_{\mathrm{S}} = 2.7\times10^{11}\mathrm{cm}^{-2}$, the hole mobility μ is $15000\mathrm{cm}^2/\mathrm{Vs}$, while the thermopower S is given [1] by the solid squares in the Fig. 1. As $T \leq 0.5$K, S is approximately linear, reflecting the domination of the diffusion thermopower S^{d} calculated by Eq. (2) using a *phenomenological* expression for p with five fitting parameters but no calculations starting from the microscopic level [1].

Our calculations, on the other hand, are based on experimental parameters using Δ and Λ as fitting parameters. These parameters are: $L = 400$Å, $L_{\mathrm{S}} = 120$Å, $L_{\mathrm{I}} = 300$Å, $x = 0.12$, $n_{\mathrm{I}} = 3.0\times10^{18}\mathrm{cm}^{-3}$, $m^* = 0.29m_e$ [1, 11]. The finite barrier is chosen to be $V_0(x) = 0.74x = 0.089$ eV as in the Ref. [21] while the alloy disorder potential $u_{\mathrm{Al}} = 0.30$ eV as in the Ref. [22]. Following the Refs. [4, 22], the other

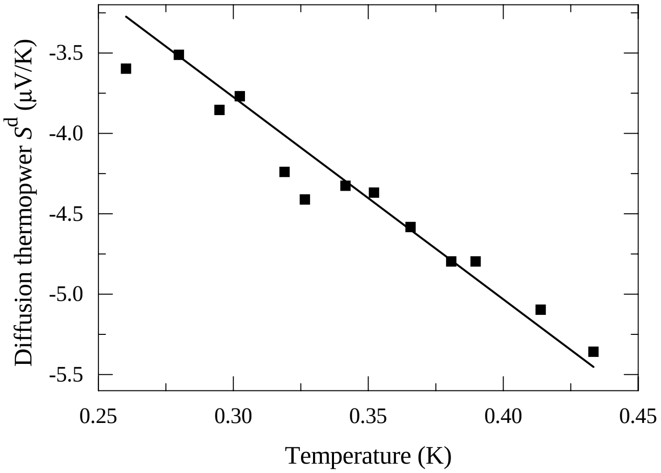

Fig. 1 Measured thermopower S (squares) reported in Ref. [1] and calculated diffusion thermopower S^{d} (solid line) of the 2D hole gas vs temperature T. Calculation parameters are $\Delta = 1.3$ Å , $\Lambda = 97$ Å, and $n_{\mathrm{I}} = 3.0 \times 10^{18}\mathrm{cm}^{-3}$.

parameters are: $a_{\mathrm{Si}} = 5.43$ Å, $a_{\mathrm{Ge}} = 5.658$ Å , $a_{\mathrm{Al}} = 5.455$ Å, $n_{\mathrm{D}} = 5.0 \times 10^{10}$ cm^{-2}, $\epsilon_{\mathrm{L}} = 12.192$, $b_{\mathrm{s}} = -2.804$ eV, $d_{\mathrm{s}} = -5.240$ eV, $c_{11} = 16.15 \times 10^{10}$ Pa, $c_{12} = 6.203 \times 10^{10}$ Pa, $c_{44} = 7.821 \times 10^{10}$ Pa and $e_{14} = 0.956 \times 10^{-2}$ $\mathrm{C/m}^2$. Detail discussions in choosing parameters are available in Ref. [4]. As a result, calculations with $\Delta = 1.3$ Å and $\Lambda = 97$ Å give $\mu = 14709$ $\mathrm{cm}^2/\mathrm{Vs}$ and S^{d}/T is -12.60 $\mu\mathrm{V/K}^2$, providing the best fit to the reported data, as seen on the Fig. 1.

It has been suggested both experimentally [17, 18, 23] and theoretically [13, 24] that $\Lambda \sim 100$ Å while Δ varies from 1 Å to 20 Å. In fact, the roughness amplitude $\Delta = 1.3$ Å is small comparing to those normally used [2, 3, 4, 5, 6], thus it is necessary to propose an interpretation for this value. It has been pointed out [17, 18] that a strained layer, as thinner than a critical thickness [25], prefer to relax by buckling which gives raise interface roughness. Consequently, Δ is found to depend strongly on the strained SiGe layer thickness [18], the Ge content of the SiGe layer [18, 23], and the cap layer thickness [18]. In our HS [1, 11], the SiGe layer with $L = 400$ Å is thick, the Ge content $x = 0.12$ is small, and the cap layer is thick ($L_{\mathrm{S}} + L_{\mathrm{I}} = 420$ Å). All of them, interestingly, supply a small Δ [18, 23]. Further, there exist in the literature many studies supporting Δ at the same order. Very small roughness amplitudes ($\Delta \simeq 1$Å) of Si/SiGe interfaces have been seen experimentally in the Ref. [23]. The same Δ were also used theoretically, including $\Delta = 2$ Å in the Ref. [13], and $\Delta = 1.78$ Å in the Ref. [24].

4.2 Scattering mechanisms and the diffusion thermopower

In order to examine the strengths of the existing scatterings in our HS, the hole mobilities limited by separated and combined scatterings are given on the Fig. 2 using the expression $\mu = e\tau(E_{\mathrm{F}})/m^*$ within the linear transport theory [9]. The parameters of the Fig. 1 are used here. The Fig. 2 indicates that in our HS, piezoelectric scattering is weak and alloy disorder is of minor important on the whole range of p_{S}. As $p_{\mathrm{S}} \geq 1.5 \times 10^{11}\mathrm{cm}^{-2}$, deformation potential and interface roughness are the dominant scatterings while in the region $p_{\mathrm{S}} \leq 1.5 \times 10^{11}\mathrm{cm}^{-2}$, remote impurity dominates. There are two reasons for the major importance of interface roughness, in spite of small Δ. First, since the barrier is small, the hole wave function penetrates deeply into the substrate. Consequently, the hole density at the barrier is finite instead of zero for the infinite barrier, thus strengthening interface roughness scattering [4]. Next, the finite barrier suppresses both alloy disorder and deformation potential scatterings, as showed by the Ref. [4].

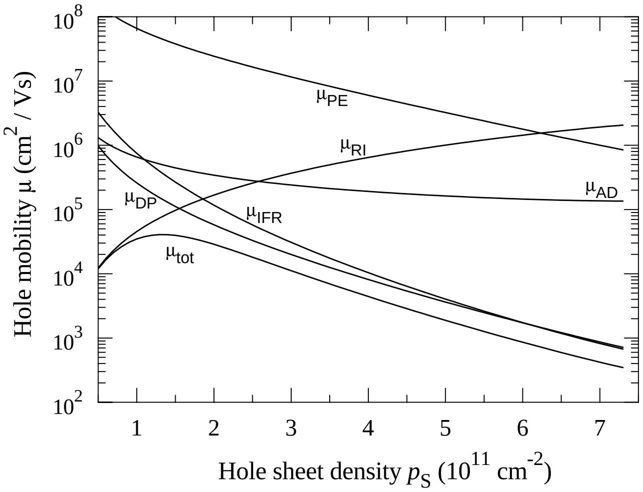

Fig. 2 Partial and total mobilities of the 2D hole gas in Si/Si$_{0.88}$Ge$_{0.12}$ HS vs hole density $p_{\rm S}$. $\mu_{\rm RI}$, $\mu_{\rm AD}$, $\mu_{\rm IFR}$, $\mu_{\rm DP}$, $\mu_{\rm PE}$ are the partial mobilities limited by remote impurity, alloy disorder, interface roughness, deformation potential, and piezoelectric, respectively. The total mobility $\mu_{\rm tot}$ is limited by all of the scatterings.

Next, we examine the partial and total $S^{\rm d}/T$ which are plotted vs. $p_{\rm S}$ on the Fig. 3 with the same parameters of Fig. 2. The notations $S^{\rm d}_{\rm RI}$, $S^{\rm d}_{\rm AD}$, $S^{\rm d}_{\rm IFR}$, $S^{\rm d}_{\rm DP}$, $S^{\rm d}_{\rm PE}$ represent the partial diffusion thermopowers due to remote impurity, alloy disorder, interface roughness, deformation potential, and piezoelectric scatterings, respectively. As mentioned above, the total $S^{\rm d}$ is a combination of the partial components, weighted by the corresponding scattering strengths. An examination of Fig. 3 reveals that $S^{\rm d}$ changes its sign at $p_{\rm S} \simeq 1.8 \times 10^{11}{\rm cm}^{-2}$, which is smaller than that reported for 2D electron gas [2, 3]. On the whole range of $p_{\rm S}$, $S^{\rm d}_{\rm PE}$ and $S^{\rm d}_{\rm IFR}$ are almost independent of $p_{\rm S}$. Differently, $S^{\rm d}_{\rm DP}$ is very negative and depends strongly on $p_{\rm S}$ as $p_{\rm S} \leq 2.0 \times 10^{11}{\rm cm}^{-2}$ before becoming independent of $p_{\rm S}$ as $p_{\rm S} \geq 4.0 \times 10^{11}{\rm cm}^{-2}$. While $S^{\rm d}_{\rm AD}$ is very small and may be neglected, $S^{\rm d}_{\rm RI}$ is the only one having large positive values.

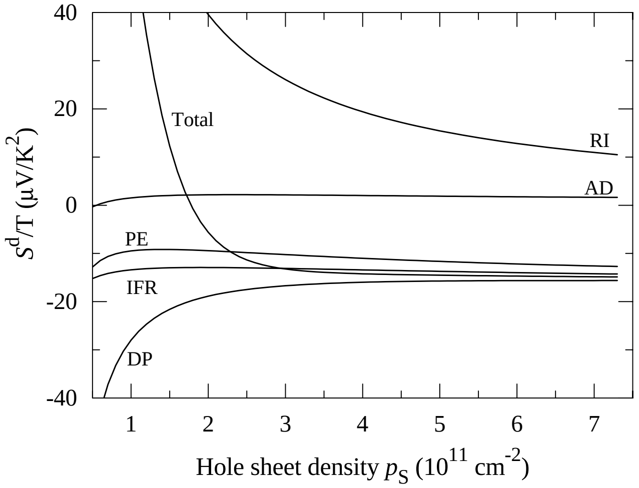

Fig. 3 Partial and total $S^{\rm d}/T$ of the Si/Si$_{0.88}$Ge$_{0.12}$ HS in Fig. 2 as functions of $p_{\rm S}$ with the parameters taken from Fig. 2. RI, AD, IFR, DP, PE are the abbreviations of remote impurity, alloy disorder, interface roughness, deformation potential, and piezoelectric scatterings, respectively.

Now we turn to another interesting issue: the possibility of changing in sign of $S^{\rm d}$ when the SiGe layer thickness L changes. While the change in sign of $S^{\rm d}$ in $n-$ type Si-MOSFET's as the carrier density varies has been addressed [2, 3], no discussion on the dependence of $S^{\rm d}$ on L has been given. A recent study [6], on the other hand, suggests that the $S^{\rm d}$ of an $n-$type GaAs quantum well can change its sign as the well thickness L changes. This possibility is a consequence of a strong piezoelectric scattering in the quantum well made by GaAs material with a large piezoelectric constant e_{14}. It may be interesting to figure out if there is such a possibility in a SiGe alloy with a smaller e_{14}?

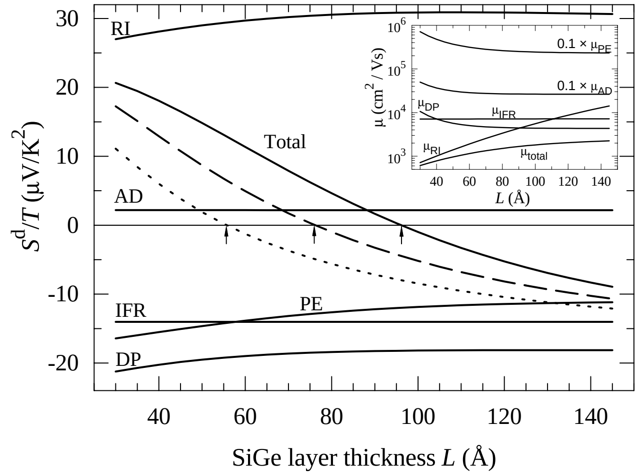

Fig. 4 Plot of partial and total $S^{\rm d}/T$ of a Si/Si$_{0.88}$Ge$_{0.12}$ HS as functions of the SiGe layer thickness L with $L_{\rm S}$ = 100Å (solid line). Dashed and dotted lines give the total $S^{\rm d}/T$ for $L_{\rm S}$ = 125Å and $L_{\rm S}$ = 150Å, respectively. The hole mobilities limited by separated and combined scatterings of this HS are given on the inset.

To answer this question, we look for experimentally attainable parameters which allow our HS to exhibit a change in sign of $S^{\rm d}$ as L changes. The following parameters are kept: $p_{\rm S} = 2.7 \times 10^{11}{\rm cm}^{-2}$, $L_{\rm I}$ = 300 Å, $x = 0.12$. The others are chosen for a weaker remote impurity scattering: $n_{\rm I} = 1 \times 10^{18}{\rm cm}^{-3}$, $L_{\rm S}$ = 100 Å, Δ = 3 Å, Λ = 100 Å. The partial and total $S^{\rm d}/T$ are plotted vs. L on the Fig. 4, which shows that the total diffusion thermopower changes its sign at the SiGe layer critical thickness $L_{\rm C} \simeq$ 96 Å.

For more information, the inset of the Fig. 4 provides the hole mobilities of the HS limited by separated and combined scatterings. It can be seen that while alloy disorder and piezoelectric scatterings are small, the others are comparable. Thus, remote impurity, deformation potential and interface roughness are important scatterings determining the total diffusion thermopower. Since nothing but $S^{\rm d}_{\rm RI} \gg 1$ (Fig. 3), we can adjust $L_{\rm C}$ by changing the strength of remote impurity scattering. There are several ways to do that, including changing the spacer thickness or impurity density. Indeed, our calculations reveal that $L_{\rm C}$ depends strongly on $L_{\rm S}$. For illustrations, the dashed line on the Fig. 4 shows that for $L_{\rm S}$ = 125 Å, $L_{\rm C} \simeq$ 76 Å. If the spacer is wider, ($L_{\rm S}$ = 150 Å), the critical thickness is even much lower: $L_{\rm C} \simeq$ 55 Å (the dotted line).

5 Conclusion

In conclusion, we present a theoretical study of the diffusion thermopower $S^{\rm d}$ in a $p-$type Si/Si$_{1-x}$Ge$_x$ lattice mismatched HS at low temperature and zero magnetic field. In the HS, deformation potential, alloy disorder, and piezoelectric scatterings are examined in comparing to the conventional scatterings. The calculated diffusion thermopower is in good agreement with a recent experiment. Further, $S^{\rm d}$ is found to depend strongly on the SiGe layer thickness L, and changes its sign as L across a critical thickness $L_{\rm C}$. The possible parameters which can affect $L_{\rm C}$ is also proposed. Deformation potential is a dominant scattering, making an important contribution to S^{d}. On the other hand, piezoelectric is weak while alloy disorder has a very small partial S^{d}. Changing the hole density, we find a sign change of S^{d} at a smaller hole density comparing to that reported previously for 2D electron gases.

Acknowledgments

The authors would like to thank Professor J. C. Maan, University of Nijmegen, The Netherlands for supplying the data used in the Fig. 1 of this paper. They also thank the referees for requiring them to be more precise in preparing this manuscript.

References

[1] C. Possanzini, R. Fletcher, M. Tsaousidou, P. T. Coleridge, R. L. Williams, Y. Feng, and J. C. Maan, Phys. Rev. B **69**, 195306 (2004).
[2] V. K. Karavolas, M. J. Smith, T. M. Fromhold, P. N. Butcher, B. G. Mulimani, B. L. Gallagher and J. P. Oxley, J. Phys.: Condens. Matter **2**, 10401 (1990).
[3] V. C. Karavolas, and P. N. Butcher, J. Phys.: Condens. Matter **3**, 2597 (1991).
[4] D. N. Quang, V. N. Tuoc, T. D. Huan, and P. N. Phong, Phys. Rev. B **70**, 195336 (2004).
[5] M.A. Sadeghzadeh, A.I. Horrell, O.A. Mironov, E.H.C. Parker, T.E. Whall, and M.J. Kearney, Appl. Phys. Lett. **76**, 2568 (2000), and references therein.
[6] S. S. Kubakaddi and K. R. Usharani, Physica E **25**, 497 (2005).
[7] R. Fletcher, V. M. Pudalov, Y. Feng, M. Tsaousidou and P. N. Butcher, Phys. Rev. B **56**, 12422 (1997).
[8] R. Fletcher, M. Tsaousidou, P. T. Coleridge, Y. Feng and Z. R. Wasilewski, Physica E **12**, 478 (2002).
[9] T. Ando, A. B. Fowler, and F. Stern, Rev. Mod. Phys. **54**, 437 (1982).
[10] Y. Okuyama and N. Tokuda, Phys. Rev. B **40**, 9744 (1989).
[11] P. T. Coleridge, R. L. Williams, Y. Feng, and P. Zawadzki, Phys. Rev. B **56**, 12764 (1997).
[12] T. Ando, J. Phys. Soc. Jpn. **51**, 3893 (1982); *ibid.* **51**, 3900 (1982).
[13] D. N. Quang, V. N. Tuoc, N. H. Tung, N. V. Minh, and P. N. Phong, Phys. Rev. B **72**, 245303 (2005).
[14] E. F. Schubert, J. M. Kuo, R. F. Kopf, H. S. Luftman, L. C. Hopkins, and N. J. Sauer, J. Appl. Phys. **67**, 1969 (1990).
[15] A. L. Efros, F. G. Pikus, and G. G. Samsonidze, Phys. Rev. B **41**, 8295 (1990).
[16] D. N. Quang and N. H. Tung, phys. stat. sol. (b) **207**, 111 (1998).
[17] R. M. Feenstra and M. A. Lutz, J. Appl. Phys. **78**, 6091 (1995).
[18] H. Yin, R. Huang, K. D. Hobart, J. Liang, Z. Suo, S. R. Shieh, T. S. Duffy, F. J. Kub, J. C. Sturm, J. Appl. Phys. **94**, 6875 (2003).
[19] G.L. Bir and G.E. Pikus, *Symmetry and Strain Induced Effects in Semiconductors* (Wiley, New York, 1974).
[20] G. Braithwaite, N. L. Mattey, E. H. C. Parker, T. E. Whall, G. Brunthaler, and G. Bauer, J. Appl. Phys. **81**, 6853 (1997).
[21] R. People and J. C. Bean, Appl. Phys. Lett. **48**, 538 (1986).
[22] B. Laikhtman and R.A. Kiehl, Phys. Rev. B **47**, 10 515 (1993).
[23] S. M. Goodnick, D. K. Ferry, C. W. Wilmsen, Z. Liliental, D. Fathy, and O. L. Krivanek, Phys. Rev. B **32**, 8171 (1985).
[24] S. Yamakawa, H. Ueno, K. Taniguchi, C. Hamaguchi, K. Miyatsuji, K. Masaki, and U. Ravaioli, J. Appl. Phys. **79**, 911 (1996).
[25] R. People and J. C. Bean, Appl. Phys. Lett. **47**, 322 (1985); *ibid.* **49**, 229 (1986).